



ZHEJIANG UNI-NE Technology CO., LTD

浙江宇力微新能源科技有限公司



U2181C Data Sheet

V 1 .2

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High Current IO+/- 2.0/2.5A HALF-BRIDGE DRIVER

General Description

The U2181C Fully operated to +600V is high voltage, high speed power MOSFET and IGBT driver with dependent high and low side referenced output channels.

The logic input is compatible with standard CMOS or LSTTL output, down to 3.3V logic. The output drivers feature a high pulse current buffer stage designed for minimum driver cross-conduction. The floating channel can be used to drive an N-channel power MOSFET or IGBT in the high side configuration which operates up to 600 volts.

Product Summary

V _{OFFSET}	600V max
I _{O+/-}	2.0 A / 2.5A
V _{CC}	5V - 20V
t _{on/off} (typ.)	200 & 180ns
Work Tem	-40 ~125°C

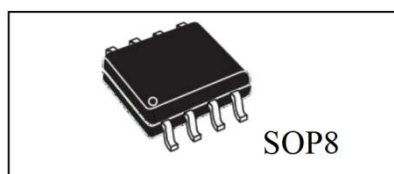
Key Features

- Floating channel designed for bootstrap operation
- Fully operational to +600V
- Tolerant to negative transient voltage dV/dt immune
- Gate drive supply range from 5 to 20V
- Undervoltage lockout
- 3.3V, 5V and 15V input logic compatible
- Matched propagation delay for both channels

Applications

- Home appliances
- Industrial applications and drives
- DC, AC, PMDC and PMAC motors
- Induction heating
- HVAC

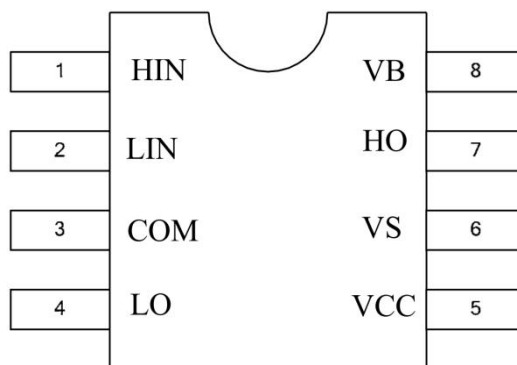
Packages



Products Information

Base Part Number	Package Type	Standard OUT		V _{OFFSET}	Logic Control
		IO+	IO-		
U2181C	SOP8	2.0A	2.5A	600V	HIN & LIN

Pin Assignments

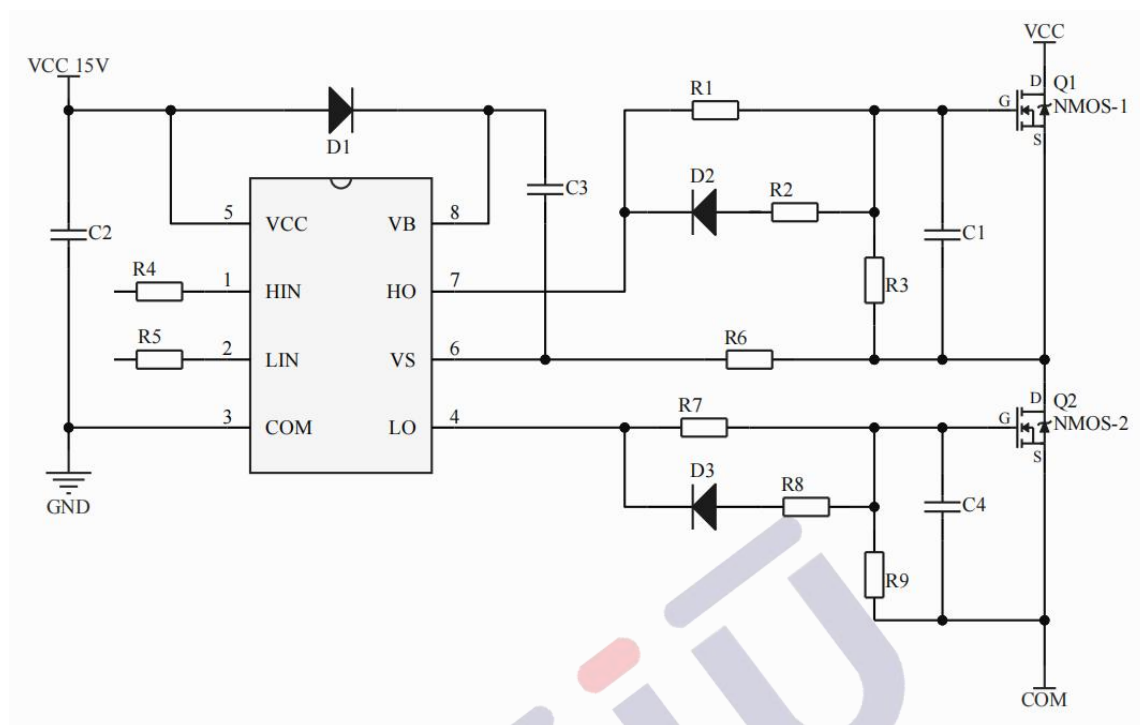


U2181C

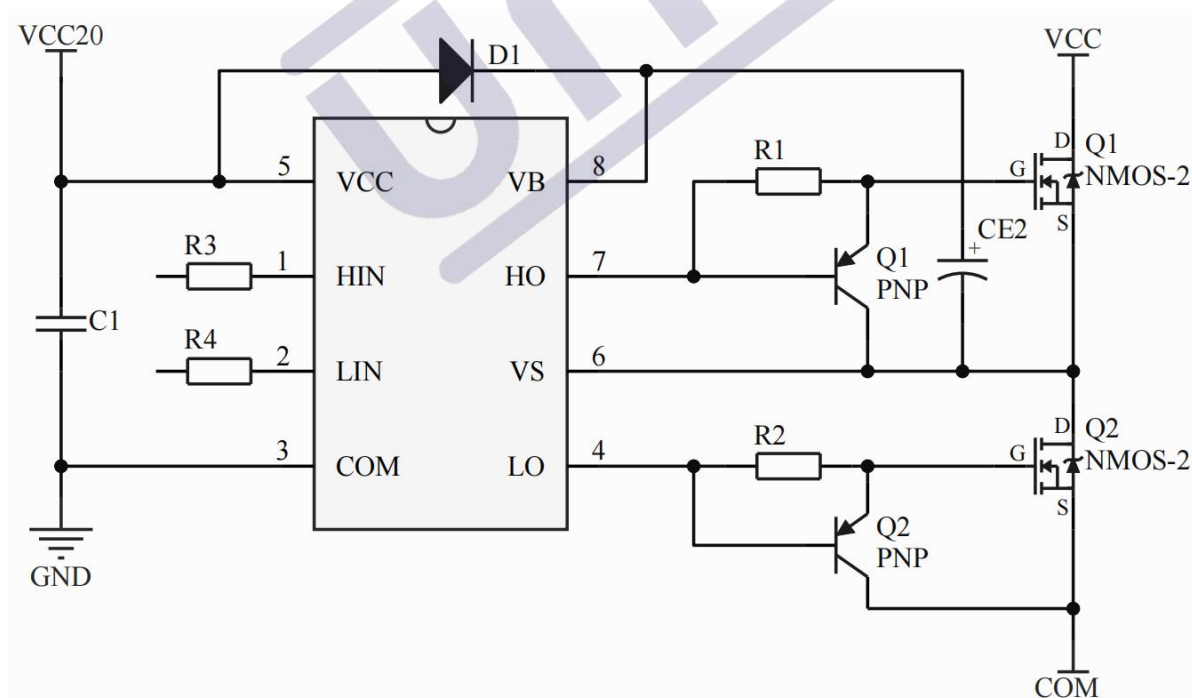
Pin Function

Number	Symbol	Type	Description
1	HIN	I	Logic input for high side gate driver outputs (HO), in phase
2	LIN	I	Logic input for low side gate driver outputs (LO), in phase
3	COM	P	Low side return
4	LO	O	Low side gate drive output
5	VCC	P	Low side and logic fixed supply
6	VS	P	High side floating supply return
7	HO	O	High side gate drive output
8	VB	P	High side floating supply

Typical Connection



Typical application



Much Big POWER application

Note: The above circuits and parameters are for reference only. The actual application circuit should be designed with the measured results in setting the paramete.

Absolute Maximum Ratings

Absolute maximum ratings indicate sustained limits beyond which damage to the device may occur. All voltage parameters are absolute voltages referenced to COM. The thermal resistance and power dissipation ratings are measured under board mounted and still air conditions.

Symbol	Definition	Min.	Max.	Units
VB	High side floating absolute voltage	-0.3	625	V
VS	High side floating supply offset voltage	VB-25	VB+0.3	
VHO	High side floating output voltage	VS-0.3	VB+0.3	
VLO	Low side output voltage	-0.3	Vcc+0.3	
Vcc	Low side and logic fixed supply voltage	-0.3	25	
VIN	Logic input voltage (HIN & LIN)	-0.3	Vcc+0.3	
dVS/dt	Allowable offset supply voltage transient	—	55	V/ns
P _D	Package power dissipation @ TA ≤ +25°C	—	0.625	W
RthJA	Thermal resistance, junction to ambient	—	200	°C/W
TJ	Junction temperature	—	150	°C
TS	Storage temperature	-55	150	
TL	Lead temperature (soldering, 10 seconds)	—	300	

Recommended Operating Conditions

The Input/Output logic timing diagram is shown in Figure 1. For proper operation the device should be used within the recommended conditions. The VS offset rating is tested with all supplies biased at 15V differential.

Symbol	Definition	Min.	Max.	Units
VB	High side floating supply absolute voltage	VS + 5	VS + 20	V
VS	High side floating supply offset voltage	-6(Note1)	600	
VHO	High side floating output voltage	VS	VB	
VLO	Low side output voltage	0	VCC	
VCC	Low side and logic fixed supply voltage	5.0	20	
VIN	Logic input voltage (HIN&LIN)	0	VCC	
TA	Ambient temperature	-40	125	°C

Note1: Logic operational for VS of -6 to +600V. Logic state held for VS of -6V to -VBS.

Electrical Characteristic

$V_{CC} = V_{BS} = V_{BIAS} = 15V$, $CL=1000pF$, $TA = 25^{\circ}C$, unless otherwise specified.

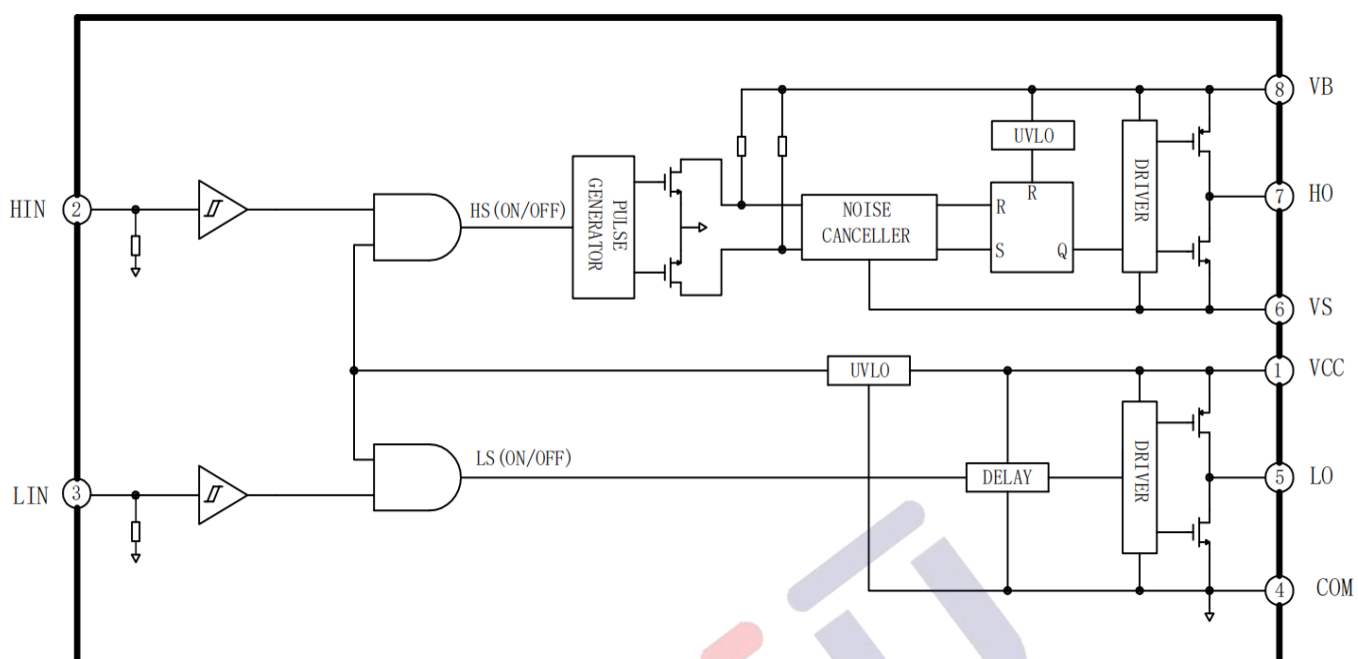
Symbol	Definition	Min.	Typ.	Max.	Units	Test Conditions
t_r	Turn-on rise time	—	20	50	ns	
t_f	Turn-off fall time	—	18	48		
t_{on}	Turn-on propagation delay	—	200	280		$V_S = 0V$
t_{off}	Turn-off propagation delay	—	180	240		$V_S = 400V$
MT	Delay matching, HS & LS turn-on/off	—	—	70		

Electrical Characteristic

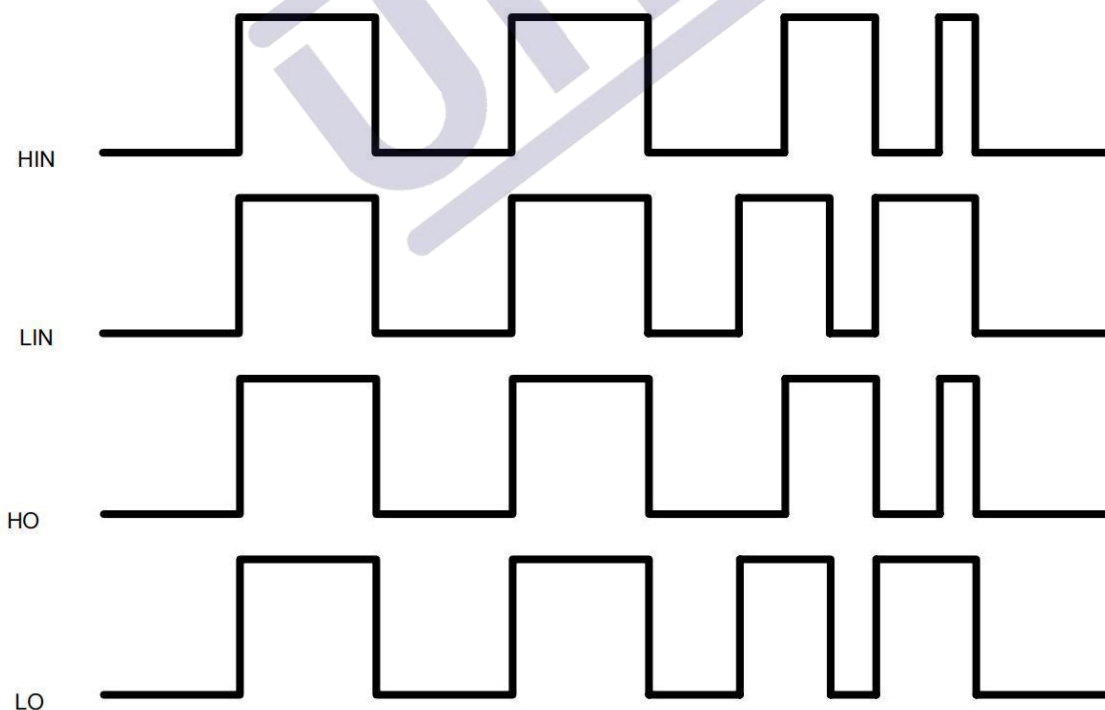
$V_{CC} = V_{BS} = V_{BIAS} = 15V$, $TA = 25^{\circ}C$, unless otherwise specified.

Symbol	Definition	Min.	Typ.	Max.	Units	Test Conditions
Low Side Power Supply Characteristics						
V _{CCUV+}	VCC supply under-voltage positive going threshold	—	4.8	—	V	
V _{CCUV-}	VCC supply under-voltage negative going threshold	—	4.5	—		
V _{CCHYS}	VCC supply under-voltage lockout hysteresis	—	0.3	—		
High Side Floating Power Supply Characteristics						
V _{BSUV+}	High side VBS supply under-voltage positive going threshold	—	4.9	—	V	
V _{BSUV-}	High side VBS supply under-voltage negative going threshold	—	4.6	—		
V _{BSUVHS}	High side VBS supply under-voltage lockout hysteresis	—	0.3	—		
I _{QCC}	Quiescent VCC supply current	—	100	—	uA	V _{in} =0V or 5V
I _{QBS}	Quiescent VBS supply current	—	32	—		V _{in} =0V or 5V
ILK	Offset supply leakage current	—	—	3		V _B = V _S = 400V
V _{IH}	Logic “1” (HO) & Logic “0” (LO) input voltage	3	—	—	V	V _{CC} =5V to 20V
V _{IL}	Logic “0” (HO) & Logic “1” (LO) input voltage	—	—	0.8		V _{CC} =5V to 20V
I _{IN+}	Logic “1” input bias current	—	20	50	uA	V _{IN} = 5V I _{IN} = 0V
I _{IN-}	Logic “0” input bias current	—	—	1		V _{IN} = 5V I _{IN} = 0V
V _{OH}	High level output voltage, V _{BIAS} - V _O	—	—	100	mV	I _o = 0A
V _{OL}	Low level output voltage, V _O	—	—	100		I _o =0A
I _{O+}	Output high short circuit pulsed current	—	2000	—	mA	V _O = 0V V _{IN} = V _{IH} PW ≤ 10 us
I _{O-}	Output low short circuit pulsed current	—	2500	—		V _O = 15V V _{IN} = V _{IL} PW ≤ 10 us

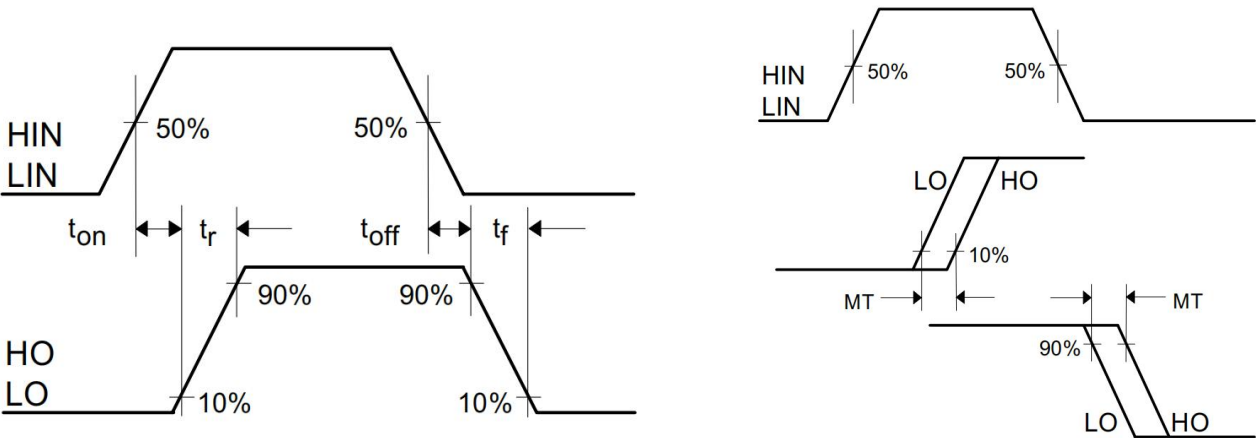
Block Diagram



Time waveform



Time waveform

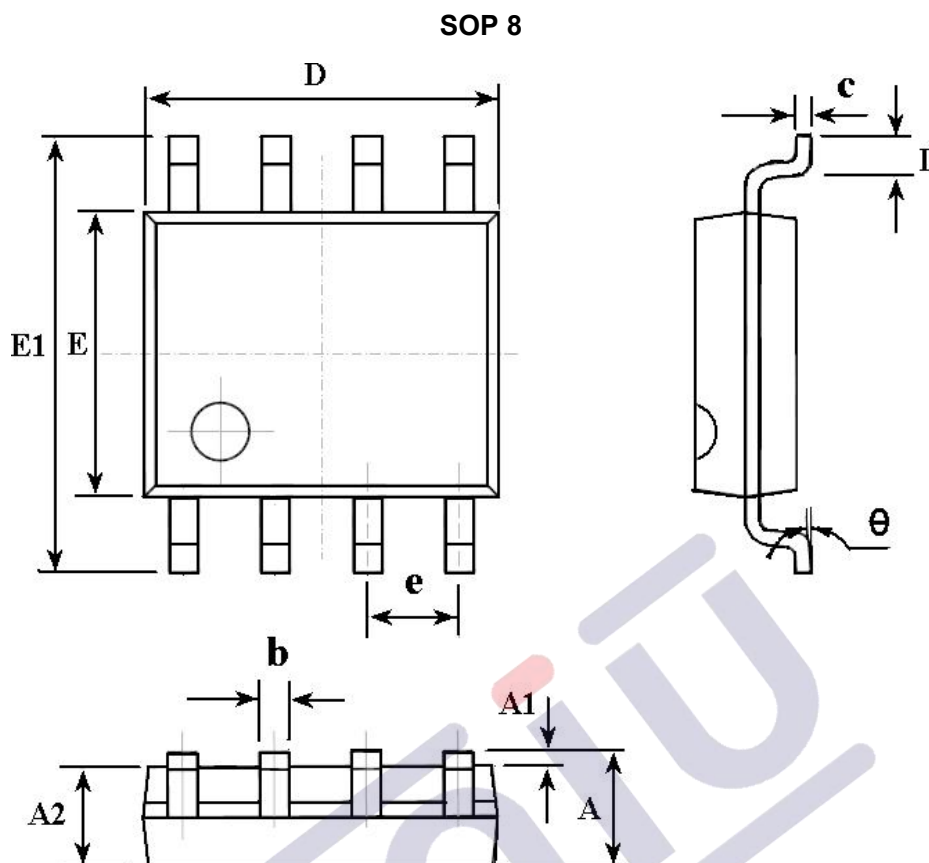


Switching Time Waveform Definitions

Delay matching time Definitions



Packaging information



Symbol	Dimensions In Millimeters	
	Min	Max
A	1.350	1.750
A1	0.100	0.250
A2	1.350	1.550
b	0.330	0.510
c	0.170	0.250
D	4.700	5.100
E	3.800	4.000
E1	5.800	6.200
e	1.270(BSC)	
L	0.400	1.270
θ	0°	8°

1、版本记录

DATE	REV.	DESCRIPTION
2018/04/19	1.0	首次发布
2021/11/04	1.1	布局调整
2023/06/18	1.2	电路调整

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